# Atlas DCA (Model DCA55) Software Revisions

| Revision | Notes |
|---|---|
| R1.0 | Original release. |
| R1.1 | Used different diode detection thresholds for diodes and diode protection on BJTs to improve Schottky detection. |
| R1.2 | Added advanced self tests for production. |
| R1.4 | Improved threshold for detection of "no component" |
| R1.5 | Reorganised string handling to make space for JFET and DM MOSFET routines.<br>Added tests for JFETs and Depletion Mode MOSFETs.<br>Defined subscript characters.<br>Added beep routine for factory test.<br>Now turns off after 5 seconds if only one message in results screen stack. |
| R1.6 | Increased BJT collector leak threshold from 0.5mA to 0.7mA.<br>Increase MOSFET drain leak threshold from 0.5mA to 1.0mA.<br>Added short circuit detection before diode tests. |
| **Above versions cannot be upgraded due to lack of active filter used in later versions.** | |
| R1.7 | New Code for V1.2 PCB to take advantage of faster active filter.<br>Improve detection of low Vf diodes. |
| R1.8 | Support for new LCD module type. |
| R1.9 | Small improvements to sensitive SCR and Triac detection. |
| R2.0 | Added BJT Leakage Measurement.<br>Increased acceptable leakage from 0.7mA to 1.25mA. |
| R2.1 | Adjustment for slow BJTs. |
| R2.2 | Small improvements to SCR and Triac detection (improved pre-test gate discharge). |
| R2.3 | Small improvements to BJT and JFET detection.<br>Now rejects leaky silicon BJTs.<br>Improved induced mains ripple rejection.<br>Added new germanium/silicon detection. |
| R2.4 | Added support for new micro type. |
| R2.5 | Improved self tests. |
| R2.5b | Support for new micro family. |
| R2.6 | Improvement to very low pinch-off JFET detection.<br>Adjusted germanium Vbe threshold.<br>Improved power management when idle. |
| R2.7 | Improved performance for high threshold MOSFETs.<br>Improved detection of darlingtons with low base-emitter resistance. |
| R2.8 | Added "Digital transistor" detection. |
| R2.9 | Increased Ge leakage current threshold from 1.25mA to 2.0mA.<br>Small adjustment to SCR thresholds.<br>Small adjustment to JFET thresholds. |
| **Dual versions from here to allow for V1.2/V2.0 and V3 PCBs to have same feature set.** | |
| R2.92/2.93 | Support new PCB V3 I/O allocation. |
| R2.94/2.95 | Allows germanium base-emitter reverse leakage current.<br>Reduce acceptable germanium collector-emitter leakage threshold to 1.5mA. |
| R2.96/2.97 | Adjusted C-E protection diode threshold to ignore leaky germaniums.<br>Increased auto-power-off period to 60 seconds. |
| R2.98/2.99 | Corrected HFE to hFE.<br>Increased contrast PWM frequency to reduce flicker. |
| R3.00/3.01 | Improvement to Ge/Si distinction for low $V_{BE}$ Si BJTs.<br>Improved factory setting of LCD contrast. |

*Please note that upgrades can only be performed by Peak Electronic Design Ltd.*
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